# **Spread Spectrum Clock Generator**

# MB88151

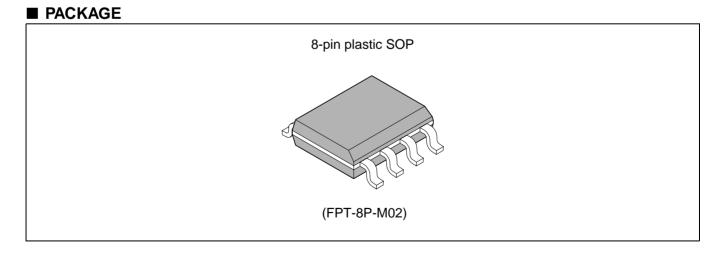
#### ■ DESCRIPTION

MB88151 is a clock generator for EMI (Electro Magnetic Interference) reduction. The peak of unnecessary radiation noise (EMI) can be attenuated by making the oscillation frequency slightly modulate periodically with the internal modulator. It corresponds to both of the center spread which modulates frequency in modulation off as Middle Centered and down spread which modulates so as not to exceed frequency in modulation off.

#### ■ FEATURES

- Input frequency : 16.6 MHz to 33.4 MHz
- Multiplication rate : 1/2, 1, 2, 4
- Output frequency : 8.3 MHz to 16.7 MHz, 16.6 MHz to 33.4 MHz, 33.3 MHz to 66.7 MHz, 66.6 MHz to 133.4 MHz
- Modulation rate :  $\pm 0.5\%$ ,  $\pm 1.5\%$  (Center spread), -1.0%, -3.0% (Down spread)
- Equipped with oscillation circuit : Range of oscillation 16.6 MHz to 33.4 MHz
- Modulation clock output Duty : 40% to 60%

(Continued)





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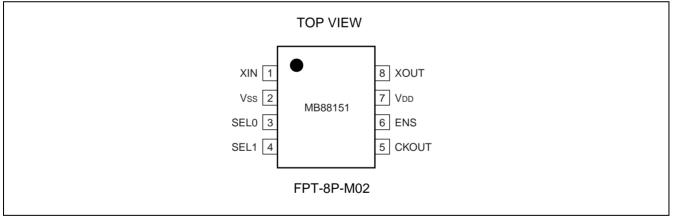
- Modulation clock
  - Cycle-Cycle Jitter
  - MB88151-100, 200 : Less than 100 ps
  - MB88151-400 : Less than 150 ps
  - MB88151-500 : Less than 200 ps
- Low current consumption by CMOS process : 5 mA (24 MHz : Typ-sample, no load)
- Power supply voltage : 3.3 V  $\pm$  0.3 V
- Operating temperature :  $-40 \ ^{\circ}C$  to  $+85 \ ^{\circ}C$
- Package : SOP 8-pin

### PRODUCT LINEUP

MB88151 has four kinds of multiplication type.

| Product     | Input frequency range  | Multiplier ratio  | Output frequency range |
|-------------|------------------------|-------------------|------------------------|
| MB88151-100 |                        | Multiplied by 1   | 16.6 MHz to 33.4 MHz   |
| MB88151-200 | - 16.6 MHz to 33.4 MHz | Multiplied by 2   | 33.3 MHz to 66.7 MHz   |
| MB88151-400 |                        | Multiplied by 4   | 66.6 MHz to 133.4 MHz  |
| MB88151-500 |                        | Multiplied by 1/2 | 8.3 MHz to 16.7 MHz    |

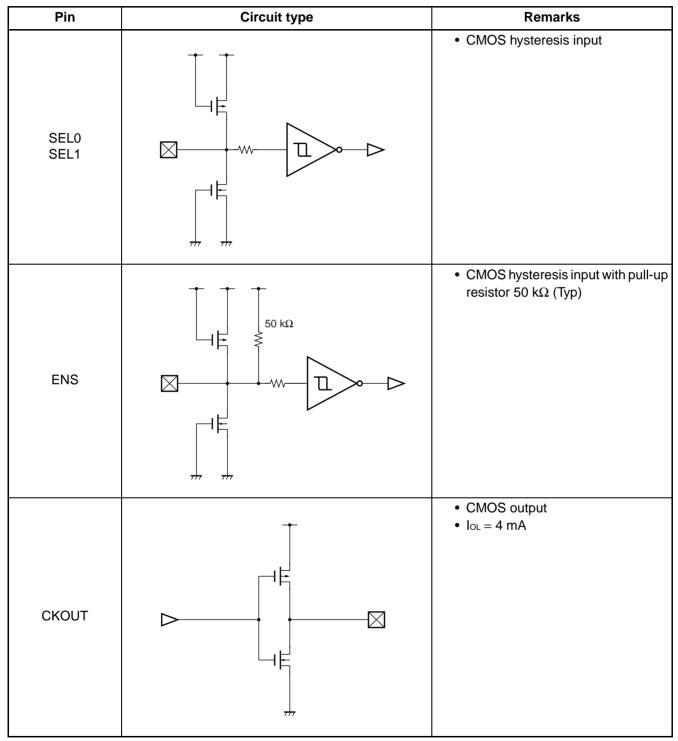
### ■ PIN ASSIGNMENT



### ■ PIN DESCRIPTION

| Pin name | I/O | Pin no. | Description   |
|----------|-----|---------|---|
| XIN      | I   | 1       | Resonator connection pin/clock input pin                |
| Vss      | —   | 2       | GND pin   |
| SEL0     | I   | 3       | Modulation rate setting pin                             |
| SEL1     | I   | 4       | Modulation rate setting pin                             |
| CKOUT    | 0   | 5       | Modulated clock output pin                              |
| ENS      | I   | 6       | Modulation enable setting pin (with pull-up resistance) |
| Vdd      | —   | 7       | Power supply voltage pin                                |
| XOUT     | 0   | 8       | Resonator connection pin                                |

#### ■ I/O CIRCUIT TYPE



Note : For XIN and XOUT pins, see "■OSCILLATION CIRCUIT".

#### ■ HANDLING DEVICES

#### **Preventing Latchup**

A latchup can occur if, on this device, (a) a voltage higher than  $V_{DD}$  or a voltage lower than  $V_{SS}$  is applied to an input or output pin or (b) a voltage higher than the rating is applied between  $V_{DD}$  and  $V_{SS}$ . The latchup, if it occurs, significantly increases the power supply current and may cause thermal destruction of an element. When you use this device, be very careful not to exceed the maximum rating.

#### Handling unused pins

Do not leave an unused input pin open, since it may cause a malfunction. Handle by, using a pull-up or pull-down resistor.

Unused output pin should be opened.

#### The attention when the external clock is used

Input the clock to XIN pin, and XOUT pin should be opened when you use the external clock. Please pay attention so that an overshoot and an undershoot do not occur to an input clock of XIN pin.

#### Power supply pins

Please design connecting the power supply pin of this device by as low impedance as possible from the current supply source.

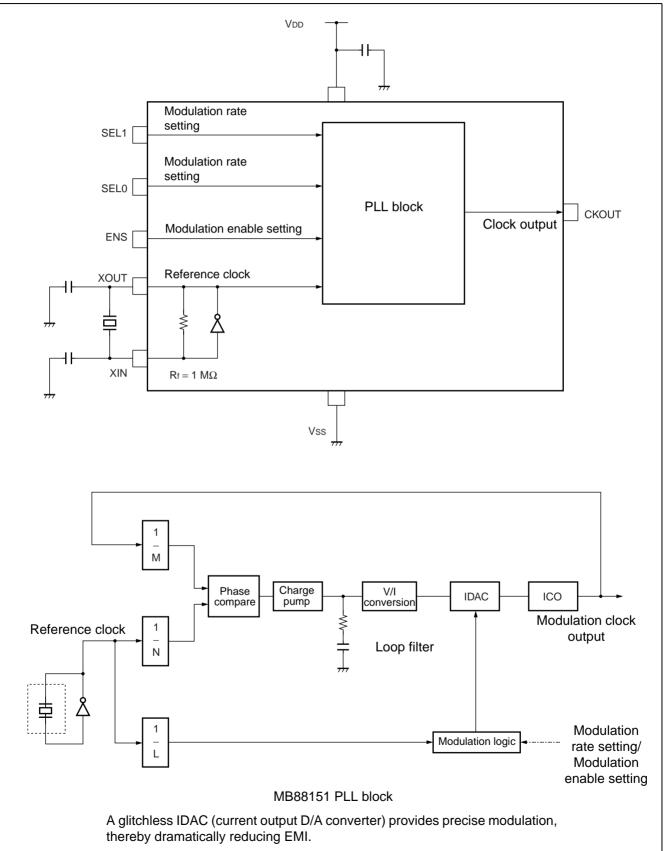
We recommend connecting electrolytic capacitor (about 10  $\mu$ F) and the ceramic capacitor (about 0.01  $\mu$ F) in parallel between Vss and V<sub>DD</sub> near the device, as a bypass capacitor.

#### **Oscillation circuit**

Noise near the XIN and XOUT pins may cause the device to malfunction. Design printed circuit boards so that electric wiring of XIN or XOUT pin and the resonator do not intersect other wiring.

Design the printed circuit board that surrounds the XIN and XOUT pins with ground.

BLOCK DIAGRAM



#### ■ PIN SETTING

When changing the pin setting, the stabilization wait time for the modulation clock is required. The stabilization wait time for the modulation clock take the maximum value of "■ ELECTRICAL CHARACTERISTICS • AC characteristics Lock-Up time".

#### ENS modulation enable setting

| ENS | Modulation    |
|-----|---------------|
| L   | No modulation |
| Н   | Modulation    |

Note : Spectrum does not spread when "L" is set to ENS. The clock with low jitter can be obtained. Because of ENS has Pull-up resistance, spectrum spread when "H" is set to it or open the terminal.

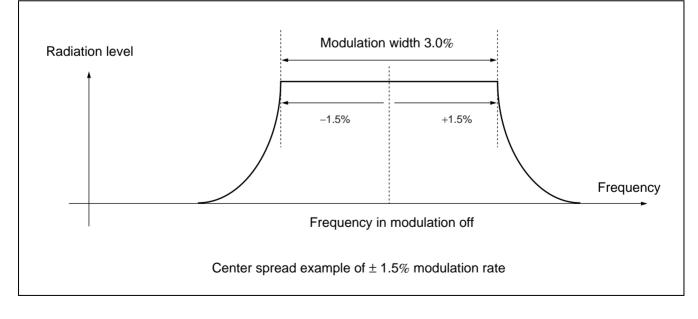
#### SEL0, SEL1 Modulation rate setting

| SEL1 | SEL0 | Modulation rate | Modulation type |
|------|------|-----------------|-----------------|
| L    | L    | ± 1.5%          | Center spread   |
| L    | Н    | ± 0.5%          | Center spread   |
| н    | L    | - 1.0%          | Down spread     |
| н    | Н    | - 3.0%          | Down spread     |

Note : The modulation rate can be changed at the level of the terminal.

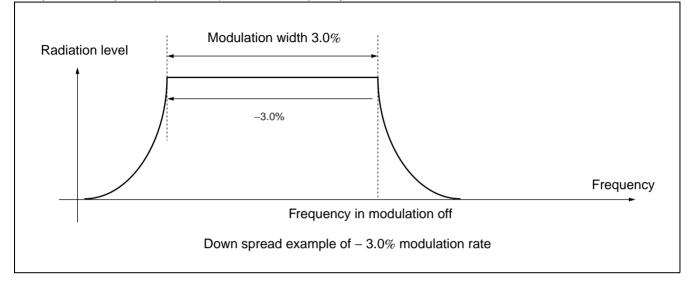
#### • Center spread

Spectrum is spread (modulated) by centering on the frequency in modulation off.



#### • Down spread

Spectrum is spread (modulated) below the frequency in modulation off.

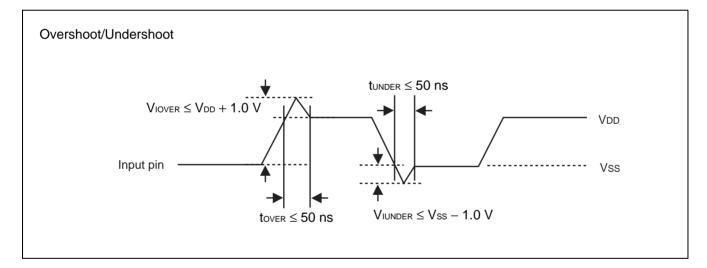


#### ABSOLUTE MAXIMUM RATINGS

| Devementer                     | Cumbal  | Rating                        |                                     |      |  |
|--------------------------------|---------|-------------------------------|-------------------------------------|------|--|
| Parameter                      | Symbol  | Min                           | Мах                                 | Unit |  |
| Power supply voltage*          | Vdd     | - 0.5                         | + 4.0                               | V    |  |
| Input voltage*                 | Vı      | Vss - 0.5                     | Vdd + 0.5                           | V    |  |
| Output voltage*                | Vo      | Vss - 0.5                     | Vdd + 0.5                           | V    |  |
| Storage temperature            | Тsт     | - 55                          | + 125                               | °C   |  |
| Operation junction temperature | TJ      | - 40                          | + 125                               | °C   |  |
| Output current                 | lo      | - 14                          | + 14                                | mA   |  |
| Overshoot                      | VIOVER  | —                             | $V_{DD}$ + 1.0 (tover $\leq$ 50 ns) | V    |  |
| Undershoot                     | Viunder | Vss-1.0 (tunder $\leq$ 50 ns) | —                                   | V    |  |

\* : The parameter is based on  $V_{SS} = 0.0 V$ .

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.



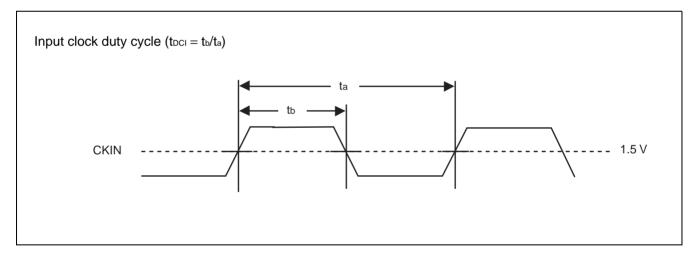
#### RECOMMENDED OPERATING CONDITIONS

|                           |        |                       |                         |                            |      | (V:                 | ss = 0.0 V) |
|---------------------------|--------|-----------------------|-------------------------|----------------------------|------|---------------------|-------------|
| Parameter                 | Symbol | Pin                   | Conditions              |                            | Unit |                     |             |
|                           | Symbol |                       | Conditions              | Min                        | Тур  | Max                 | Unit        |
| Power supply voltage      | Vdd    | Vdd                   |                         | 3.0                        | 3.3  | 3.6                 | V           |
| "H" level input voltage   | Vін    | XIN,                  |                         | $V_{\text{DD}} 	imes 0.80$ | _    | Vdd + 0.3           | V           |
| "L" level input voltage   | Vil    | SEL0,<br>SEL1,<br>ENS |                         | Vss                        |      | $V_{DD} 	imes 0.20$ | V           |
| Input clock<br>duty cycle | tDCI   | XIN                   | 16.6 MHz to<br>33.4 MHz | 40                         | 50   | 60                  | %           |
| Operating temperature     | Та     |                       |                         | - 40                       | _    | + 85                | °C          |

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.



## ■ ELECTRICAL CHARACTERISTICS

• DC Characteristics

(Ta = - 40  $^{\circ}C$  to ~+ 85  $^{\circ}C,~V_{\text{DD}}$  = 3.3 V  $\pm$  0.3 V, Vss = 0.0 V)

| Parameter                | Symbol Pin           |                               | Conditions  | Value               |             |     | Unit |
|--------------------------|----------------------|-------------------------------|---|---------------------|-------------|-----|------|
| Falameter                | Symbol               |                               |   | Min                 | Min Typ Max |     | Unit |
| Power supply current     | lcc                  | Vdd                           | No load capacitance at<br>output 24 MHz<br>MB88151-100                  |                     | 5.0         | 7.0 | mA   |
|                          | Vон                  | CKOUT                         | "H" level output,<br>Іон = − 4 mA                                       | $V_{\text{DD}}-0.5$ |             | Vdd | V    |
| Output voltage           | Vol                  | CROOT                         | "L" level output,<br>Io∟ = 4 mA   | Vss                 | _           | 0.4 | V    |
| Output impedance         | Zo                   | CKOUT                         | 8.3 MHz to 133.4 MHz  | —                   | 45          | —   | Ω    |
| Input capacitance        | CIN                  | XIN,<br>SEL0,<br>SEL1,<br>ENS | $Ta = +25 \ ^{\circ}C,$<br>$V_{DD} = V_{I} = 0.0 \ V,$<br>$f = 1 \ MHz$ |                     |             | 16  | pF   |
|                          | C∟ CKOU <sup>-</sup> |                               | 8.3 MHz to 66.7 MHz   | —                   | —           | 15  |      |
| Load capacitance         |                      | CKOUT                         | 66.7 MHz to 100 MHz   | —                   |             | 10  | pF   |
|                          |                      |                               | 100 MHz to 133.4 MHz  | —                   |             | 7   |      |
| Input pull-up resistance | Rpu                  | ENS                           | $V_{\text{IL}} = 0.0 \text{ V}$   | 25                  | 50          | 200 | kΩ   |

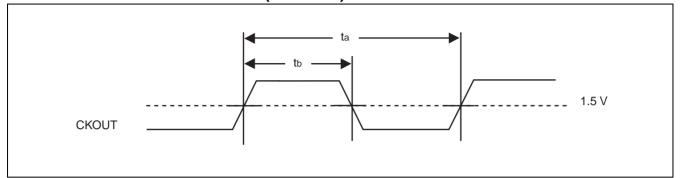
• AC Characteristics

|                         |           | Dia  |   | Value |      |       |       |  |
|-------------------------|-----------|--|---|-------|------|-------|-------|--|
| Parameter               | Symbol    | Pin  | Conditions  | Min   | Тур  | Max   | Unit  |  |
| Oscillation frequency   | fx        | XIN,<br>XOUT   | Fundamental oscillation   | 16.6  | _    | 33.4  | MHz   |  |
| Input frequency         | fin       | XIN  | External clock input  | 16.6  | —    | 33.4  | MHz   |  |
|                         |           |  | MB88151-100<br>(Multiply by 1)  | 16.6  | _    | 33.4  |       |  |
|                         | fouт      | CKOUT  | MB88151-200<br>(Multiply by 2)  | 33.3  | _    | 66.7  | – MHz |  |
| Output frequency        | IOUT      | CKOUT  | MB88151-400<br>(Multiply by 4)  | 66.6  |      | 133.4 |       |  |
|                         |           |  | MB88151-500<br>(2-frequency division)   | 8.3   | _    | 16.7  |       |  |
| Output slew rate        | SR        | СКОИТ  | 0.4 V to 2.4 V<br>Load capacitance 15 pF  | 0.4   | _    | 4.0   | V/ns  |  |
| Output clock duty cycle | tDCC      | CKOUT  | 1.5 V   | 40    | —    | 60    | %     |  |
| Modulation frequency    | fмор      | CKOUT  | —   |       | 12.5 |       | kHz   |  |
| Lock-Up time            | tlк       | CKOUT  | —   |       | 2    | 5     | ms    |  |
| Cycle-cycle jitter      | t.c CKOUT |  | $\begin{array}{l} \text{MB88151-100, 200} \\ \text{No load capacitance,} \\ \text{Ta} = + 25 \ ^\circ\text{C}, \\ \text{V}_{\text{DD}} = 3.3 \ \text{V}, \\ \text{Standard deviation} \ \sigma \end{array}$ | _     |      | 100   |       |  |
|                         |           | $\begin{array}{l} \text{MB88151-400} \\ \text{No load capacitance,} \\ \text{Ta} = + 25 \ ^\circ\text{C}, \\ \text{V}_{\text{DD}} = 3.3 \ \text{V}, \\ \text{Standard deviation} \ \sigma \end{array}$ |   |       | 150  | ps    |       |  |
|                         |           | $\begin{array}{l} \text{MB88151-500} \\ \text{No load capacitance,} \\ \text{Ta} = + 25 \ ^\circ\text{C}, \\ \text{V}_{\text{DD}} = 3.3 \ \text{V}, \\ \text{Standard deviation} \ \sigma \end{array}$ | _   |       | 200  |       |       |  |

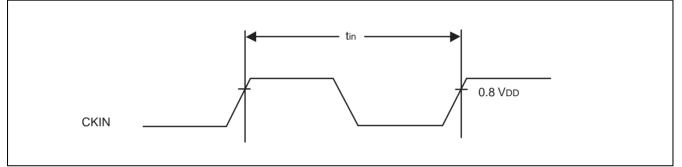
(Ta = - 40  $^{\circ}C$  to ~+ 85  $^{\circ}C,~V_{\text{DD}}$  = 3.3 V  $\pm$  0.3 V, Vss = 0.0 V)

Note : The modulation clock stabilization wait time is required after the power is turned on, the IC recovers from power saving, or after FREQ (frequency range) or ENS (modulation ON/OFF) setting is changed. For the modulation clock stabilization wait time, assign the maximum value for lock-up time.

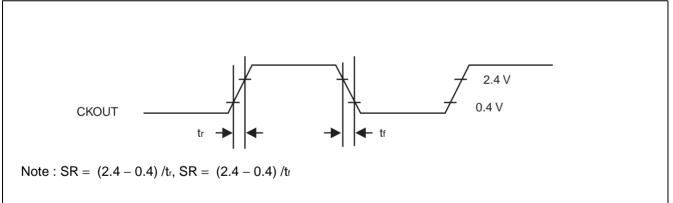
### ■ OUTPUT CLOCK DUTY CYCLE (t<sub>DCC</sub> = t<sub>b</sub>/t<sub>a</sub>)



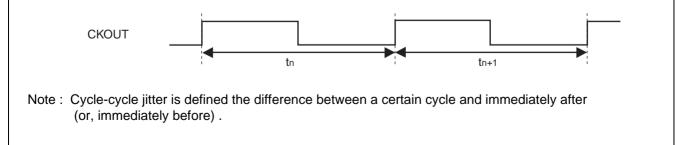
## ■ INPUT FREQUENCY (fin = 1/tin)



# ■ OUTPUT SLEW RATE (SR)

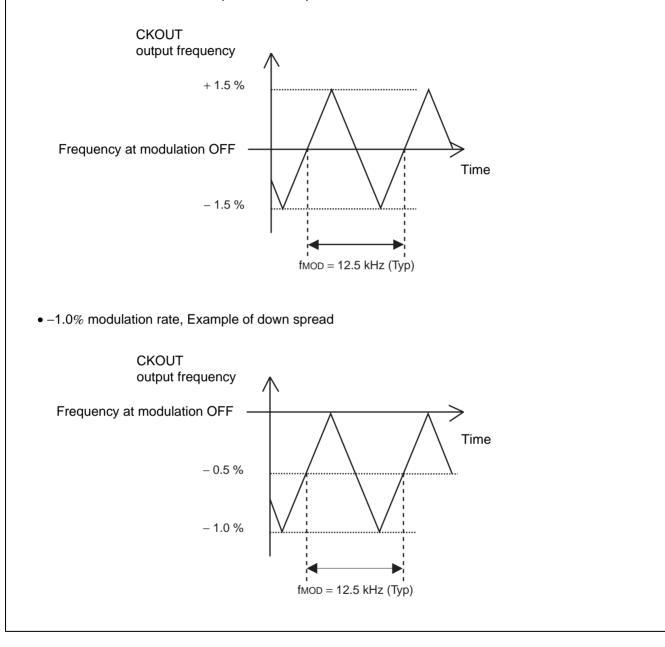


### ■ CYCLE-CYCLE JITTER (t<sub>JC</sub> = | t<sub>n</sub> - t<sub>n+1</sub> |)

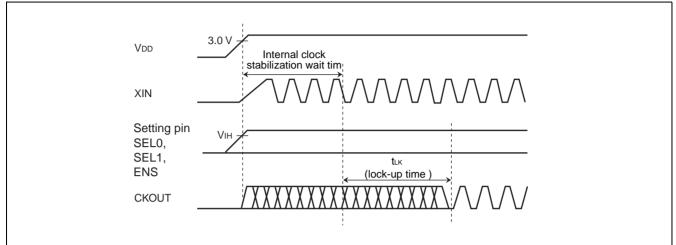


#### ■ MODULATION WAVEFORM

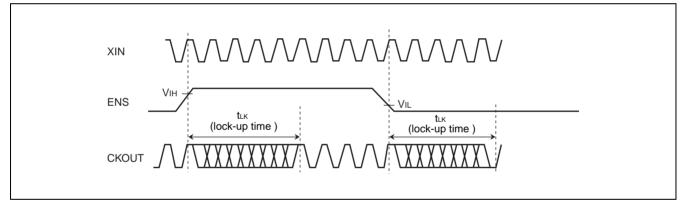
• ±1.5% modulation rate, Example of center spread



### ■ LOCK-UP TIME



If the setting pin is fixed at the "H" or "L" level, the maximum time after the power is turned on until the set clock signal is output from CKOUT pin is (the stabilization wait time of input clock to XIN pin) + (the lock-up time "tLK"). For the input clock stabilization time, check the characteristics of the resonator or oscillator used.



For modulation enable control using the ENS pin during normal operation, the set clock signal is output from CKOUT pin at most the lock-up time ( $t_{LK}$ ) after the level at the ENS pin is determined.

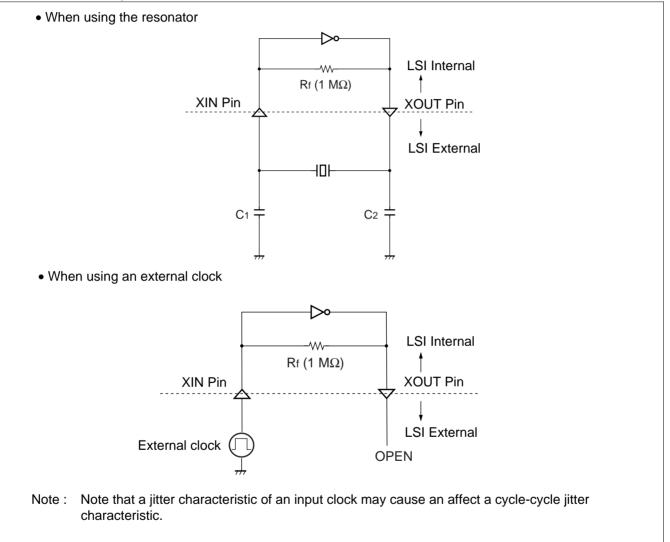
Note : When the pin setting is changed, the CKOUT pin output clock stabilization time is required. Until the output clock signal becomes stable, the output frequency, output clock duty cycle, modulation period, and cycle-cycle jitter cannot be guaranteed. It is therefore advisable to perform processing such as cancelling a reset of the device at the succeeding stage after the lock-up time.

#### OSCILLATION CIRCUIT

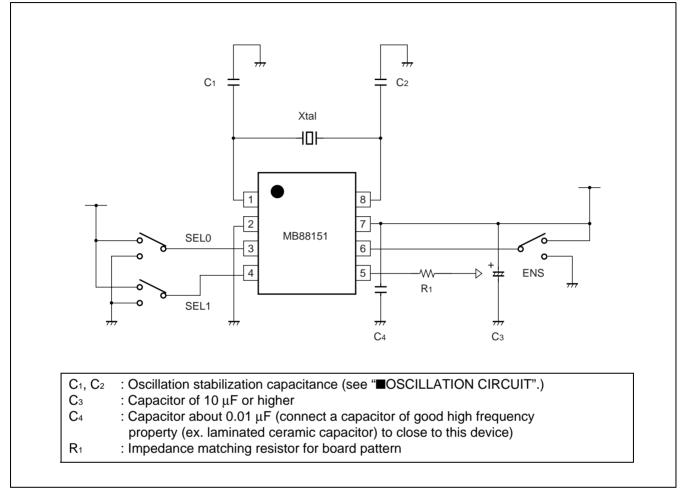
The figure below shows the connection example about general resonator. The oscillation circuit has the built-in resistance  $(1 \text{ M}\Omega)$ . The value of capacity (C<sub>1</sub> and C<sub>2</sub>) is required adjusting to the most suitable value of individual resonator.

The most suitable value is different by individual resonator. Please refer to the resonator manufacturer which you use for the most suitable value.

Input the clock to XIN pin, and do not connect anything with XOUT pin if you use the external clock (you do not use the resonator).



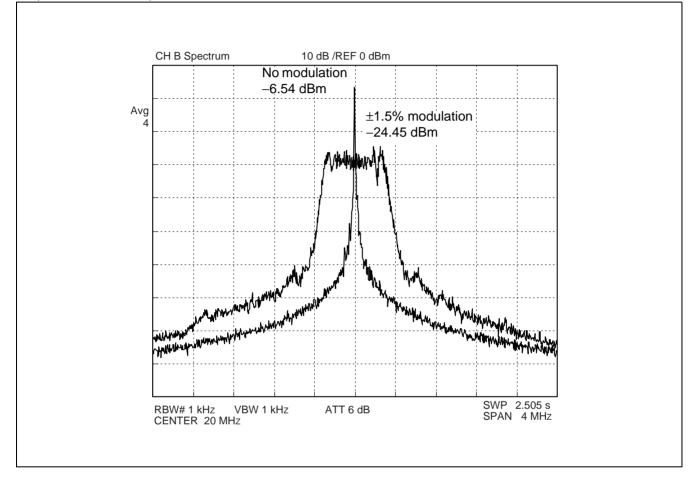
### ■ INTERCONNECTION CIRCUIT EXAMPLE



#### SPECTRUM EXAMPLE CHARACTERISTICS

The condition of the examples of the characteristic is shown as follows : Input frequency = 20 MHz (Output frequency = 20 MHz : Using MB88151-100 (Multiply by 1)), Power - supply voltage = 3.3 V, None load capacity, Modulation rate =  $\pm$  1.5% (center spread).

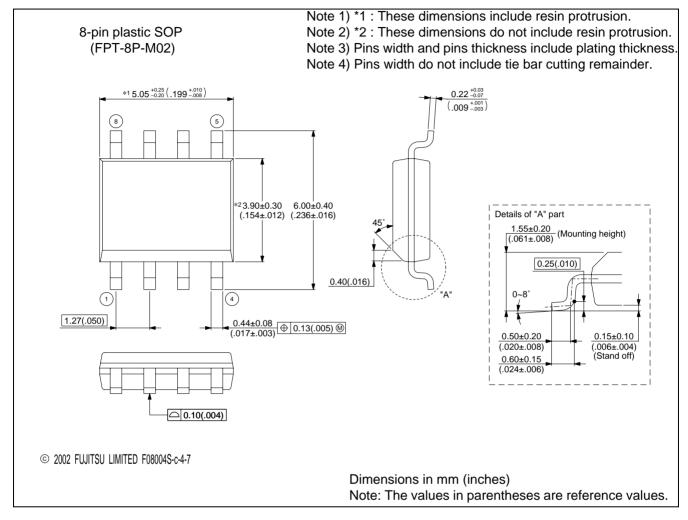
Spectrum analyzer HP4396B is connected with CKOUT. The result of the measurement with RBW = 1 kHz (ATT use for -6dB).



### ■ ORDERING INFORMATION

| Part number  | Input frequency range   | Multiplier<br>ratio  | Output frequency<br>range  | Package                              | Remarks                       |
|--|-------------------------|--|--|--------------------------------------|-------------------------------|
| MB88151PNF-G-100-JNE1<br>MB88151PNF-G-200-JNE1<br>MB88151PNF-G-400-JNE1<br>MB88151PNF-G-500-JNE1             |                         | Multiplied by 1<br>Multiplied by 2<br>Multiplied by 4<br>Multiplied by 1/2 | 16.6 MHz to 33.4 MHz<br>33.3 MHz to 66.7 MHz<br>66.6 MHz to 133.4 MHz<br>8.3 MHz to 16.7 MHz | 8-pin plastic<br>SOP<br>(FPT-8P-M02) |                               |
| MB88151PNF-G-100-JN-EFE1<br>MB88151PNF-G-200-JN-EFE1<br>MB88151PNF-G-400-JN-EFE1<br>MB88151PNF-G-500-JN-EFE1 | 16.6 MHz to<br>33.4 MHz | Multiplied by 1<br>Multiplied by 2<br>Multiplied by 4<br>Multiplied by 1/2 | 16.6 MHz to 33.4 MHz<br>33.3 MHz to 66.7 MHz<br>66.6 MHz to 133.4 MHz<br>8.3 MHz to 16.7 MHz | 8-pin plastic<br>SOP<br>(FPT-8P-M02) | Emboss<br>taping<br>(EF type) |
| MB88151PNF-G-100-JN-ERE1<br>MB88151PNF-G-200-JN-ERE1<br>MB88151PNF-G-400-JN-ERE1<br>MB88151PNF-G-500-JN-ERE1 |                         | Multiplied by 1<br>Multiplied by 2<br>Multiplied by 4<br>Multiplied by 1/2 | 16.6 MHz to 33.4 MHz<br>33.3 MHz to 66.7 MHz<br>66.6 MHz to 133.4 MHz<br>8.3 MHz to 16.7 MHz | 8-pin plastic<br>SOP<br>(FPT-8P-M02) | Emboss<br>taping<br>(ER type) |





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